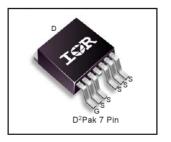
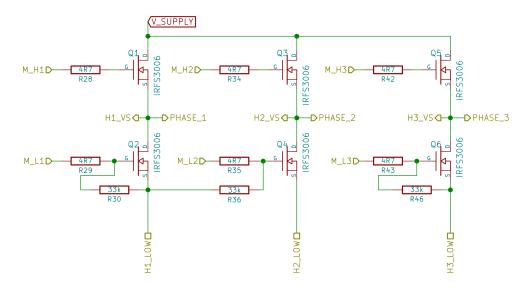


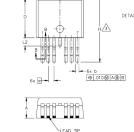
HEXFET® Power MOSFET



V _{DSS}	60V
R _{DS(on)} typ.	1.5m Ω
max.	$2.1 m\Omega$
I _D (Silicon Limited)	293A①
I _{D (Package Limited)}	240A



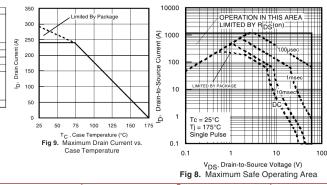




SEATING PLANE

c → -// ±.004⊗B

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	293①	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	207 ①	A
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	240	_ ^
I _{DM}	Pulsed Drain Current ②	1172	
P _D @ T _C = 25°C	Maximum Power Dissipation	375	W
	Linear Derating Factor	2.5	W/°C
V _{gs}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery ®	11	V/ns
T,	Operating Junction and	-55 to + 175	
T _{STG}	Storage Temperature Range		⊸°C
	Soldering Temperature, for 10 seconds	300	
	(1.6mm from case)		1
	Mounting torque, 6-32 or M3 screw	10lb+in (1.1N+m)	



Benjamin Vedder		
Sheet: /Power MOS		
File: mosfets.sch		

SFETS/

Title:	BLDC	Driver	4.6

Size: A4	Date: 25	Aug 2014	Rev: 4.6
KiCad E.D.A. kid	ad (2014-:	LO-11 BZR 5175)-product	ld: 2/7
4		5	•

